Muneyasu Suzuki

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/3554244/publications.pdf Version: 2024-02-01



#	Article	IF	CITATIONS
1	Synthesis of Pb(Zr, Ti)O3 fine ceramic powder at room temperature by dry mechanochemical solid-state reaction evaluated using synchrotron radiation X-ray diffraction. Japanese Journal of Applied Physics, 2021, 60, SFFA02.	1.5	4
2	Synchrotron radiation X-ray diffraction evidence for nature of chemical bonds in Bi ₄ Ti ₃ O ₁₂ ceramic powders and grain-orientation mechanism of their films formed by aerosol deposition method. Japanese Journal of Applied Physics, 2020, 59, SPPA04.	1.5	4
3	Aggregate ceramic films produced at room temperature by press forming. Journal of the American Ceramic Society, 2020, 103, 3479-3492.	3.8	0
4	Effect of starting powder morphology on film texture for bismuth layer-structured ferroelectrics prepared by aerosol deposition method. Japanese Journal of Applied Physics, 2017, 56, 06GH02.	1.5	10
5	Polarization and leakage current properties of high quality bismuth sodium titanate single crystals and polycrystalline ceramics. Journal of the Ceramic Society of Japan, 2015, 123, 9-16.	1.1	5
6	Polarization and leakage current properties of self-supported bismuth sodium titanate ceramic films deposited by aerosol deposition method. Journal of the Ceramic Society of Japan, 2013, 121, 664-669.	1.1	4
7	Polarization Properties of Bismuth Strontium Tantalate Ceramic Films Deposited by Aerosol Deposition Method. Japanese Journal of Applied Physics, 2012, 51, 09LA17.	1.5	2
8	Anisotropic electrical properties in bismuth layer structured dielectrics with natural super lattice structure. Applied Physics Letters, 2012, 101, .	3.3	2
9	Polarization Properties of Bismuth Strontium Tantalate Ceramic Films Deposited by Aerosol Deposition Method. Japanese Journal of Applied Physics, 2012, 51, 09LA17.	1.5	2
10	Ferroelectric Polarization Properties in High-Performance Bismuth Sodium Titanate Single Crystals. Key Engineering Materials, 2011, 485, 7-10.	0.4	1
11	Fabrication and Characterization of Optical Micro-Electro-Mechanical System Scanning Devices Using BaTiO ₃ -Based Lead-Free Piezoelectric-Coated Substrate Sheet by Aerosol Deposition. Japanese Journal of Applied Physics, 2011, 50, 09ND19.	1.5	15
12	Fabrication and Characterization of Optical Micro-Electro-Mechanical System Scanning Devices Using BaTiO3-Based Lead-Free Piezoelectric-Coated Substrate Sheet by Aerosol Deposition. Japanese Journal of Applied Physics, 2011, 50, 09ND19.	1.5	5
13	Polarization and leakage current properties of bismuth sodium titanate ceramic films deposited by aerosol deposition method. Journal of the Ceramic Society of Japan, 2010, 118, 899-902.	1.1	13
14	Polarization and piezoelectric properties of grain-oriented ferroelectric Bi5FeTi3O15 ceramics prepared by magnetic-field-assisted electrophoretic deposition method. Journal of Electroceramics, 2010, 24, 91-96.	2.0	6
15	Structural and piezoelectric properties of high-density (Bi0.5K0.5)TiO3–BiFeO3 ceramics. Journal of Applied Physics, 2010, 108, .	2.5	73
16	Polarization and Piezoelectric Properties of High Performance Bismuth Sodium Titanate Single Crystals Grown by High-Oxygen-Pressure Flux Method. Japanese Journal of Applied Physics, 2010, 49, 09MD09.	1.5	36
17	Temperature Dependence of Dielectric Properties of Barium Titanate Ceramic Films Prepared by Aerosol Deposition Method. Japanese Journal of Applied Physics, 2010, 49, 09MA10.	1.5	18
18	Temperature dependence of piezoelectric properties on Nd and V co-substituted Bi4Ti3O12 ceramics for ceramic resonator applications. Ceramics International, 2009, 35, 163-167.	4.8	11

#	Article	IF	CITATIONS
19	Ferroelectric Properties and Nano-Scaled Domain Structures in (1-x)BiFeO3-xBaTiO3 (0.33 < x <) Tj ETQq1	1 0.78431 0.6	4 rgBT /Overla
20	Electric-field-induced giant strain in Bi0.5Na0.5TiO3-based single crystals: Influence of high-oxygen-pressure annealing. Journal of the Ceramic Society of Japan, 2009, 117, 32-36.	1.1	13
21	Bismuth layerâ€structured ferroelectric ceramics with high mechanical quality factor. Electronics and Communications in Japan, 2008, 91, 39-45.	0.5	6
22	Temperature dependences of piezoelectric properties of vanadium substituted SrBi2Nb2O9 ceramics with grain orientation. Ceramics International, 2008, 34, 741-744.	4.8	6
23	Low strain sensitivity of the dielectric property of pyrochlore Bi–Zn–Nb–O films. Applied Physics Letters, 2008, 92, 182901.	3.3	11
24	Effects of Oxygen Annealing on Dielectric Properties of LuFeCuO ₄ . Japanese Journal of Applied Physics, 2008, 47, 8464.	1.5	12
25	Large electric-field-induced strain in Bi0.5Na0.5TiO3–Bi0.5K0.5TiO3 solid solution single crystals. Applied Physics Letters, 2008, 93, .	3.3	51
26	Grain-Orientation Control of Bi ₅ FeTi ₃ O ₁₅ Ceramics Prepared by Magnetic-Field-Assisted Electrophoretic Deposition Method. Key Engineering Materials, 2008, 388, 205-208.	0.4	1
27	High-Performance Bi _{0.5} Na _{0.5} TiO ₃ Single Crystals Grown by High-Oxygen-Pressure Flux Method. Japanese Journal of Applied Physics, 2008, 47, 7623.	1.5	66
28	Enhanced piezoelectric properties of grain-oriented Bi4Ti3O12–BaBi4Ti4O15 ceramics obtained by magnetic-field-assisted electrophoretic deposition method. Journal of Applied Physics, 2008, 104, .	2.5	19
29	Ferroelectric polarization and piezoelectric properties of layer-structured K0.5Bi4.5Ti4O15 single crystals. Applied Physics Letters, 2008, 93, 032904.	3.3	34
30	Giant strain in lead-free (Bi0.5Na0.5)TiO3-based single crystals. Applied Physics Letters, 2008, 92, .	3.3	129
31	High-quality single crystal growth of Bi-based perovskite ferroelectrics based on defect chemistry. Journal of the Ceramic Society of Japan, 2008, 116, 994-1001.	1.1	26
32	Microstructures related to the ferroelectric properties in BiFeO3-BaTiO3. Transactions of the Materials Research Society of Japan, 2008, 33, 27-30.	0.2	8
33	Effects of Oxygen Pressure during Crystal Growth on the Polarization Properties in Bi4Ti3O12 Single Crystals. Transactions of the Materials Research Society of Japan, 2008, 33, 53-56.	0.2	0
34	High-oxygen-pressure crystal growth of ferroelectric Bi4Ti3O12 single crystals. Applied Physics Letters, 2007, 91, 162909.	3.3	58
35	The Piezoelectric Properties of La ₂ O ₃ Doped (Bi _{1/2} Na _{1/2})TiO ₃ –(Bi _{1/2} K _{1/2})TiO _{3< Ferroelectrics, 2007, 358, 134-138.}	/subøæerai	mic s
36	Piezoelectric Properties of V and Ba Substituted SrBi ₂ Nb ₂ O ₉ Ceramics. Ferroelectrics, 2007, 358, 148-152.	0.6	5

MUNEYASU SUZUKI

#	Article	IF	CITATIONS
37	Ferroelectric Property of Bi ₃ TiTaO ₉ Based Ceramics with Nd Substitution. Ferroelectrics, 2007, 356, 62-66.	0.6	5
38	MOCVD growth of epitaxial pyrochlore Bi2Ti2O7 thin film. Journal of the European Ceramic Society, 2006, 26, 2155-2159.	5.7	3
39	MOCVD of Single-Axisc-Oriented Strontium Bismuth Titanate Thin Films and Their Electrical Properties. Chemical Vapor Deposition, 2006, 12, 136-142.	1.3	11
40	Growth Behavior ofc-Axis-Oriented Epitaxial SrBi2Ta2O9Films on SrTiO3Substrates with Atomic Scale Step Structure. Japanese Journal of Applied Physics, 2006, 45, L138-L141.	1.5	8
41	PROPERTIES OF A NOVEL BISMUTH PERCURSOR FOR MOCVD. Integrated Ferroelectrics, 2006, 84, 197-202.	0.7	3
42	Thickness dependence of dielectric properties in bismuth layer-structured dielectrics. Applied Physics Letters, 2006, 89, 082901.	3.3	39
43	Polarization comparison of Pb(Zr,Ti)O3 and Bi4Ti3O12-based ferroelectrics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 118, 23-27.	3.5	10
44	MOCVD Growth of Bi1.5Zn1.0Nb1.5O7(BZN) Epitaxial Thin Films and Their Electrical Properties. Japanese Journal of Applied Physics, 2005, 44, 6957-6959.	1.5	17
45	Growth of Pyrochlore Bi2Ti2O7 Epitaxial Films and Their Electrical Characterization. Integrated Ferroelectrics, 2004, 67, 201-209.	0.7	4
46	Effect of Deposition Temperature and Post-Heat-Treatment Condition on the Characteristics of (100)-Self-Orientation LaNiO ₃ Films Prepared by RF Magnetron Sputter Deposition. Materials Research Society Symposia Proceedings, 2004, 833, 57.	0.1	4
47	Piezoelectric Properties of Lanthanum Modified Bi ₃ TiTaO ₉ Ceramics. Key Engineering Materials, 2003, 248, 11-14.	0.4	9
48	Bi3-xMxTiTaO9(M = La or Nd) Ceramics with High Mechanical Quality FactorQm. Japanese Journal of Applied Physics, 2003, 42, 6090-6093.	1.5	79
49	Direct Crystallization and Characterization of Bi3TiTaO9Thin Films Prepared by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2002, 41, 6825-6828.	1.5	1
50	Effect of the Annealing Temperature on Dielectric Properties of Bi _{1.5} 2n _{1.0} Nb _{1.5} O _{7Films Prepared by MOCVD. Key Engineering Materials, 0, 388, 175-178.}	t; 0.4	0
51	Temperature Dependency of Dielectric Properties in Epitaxially Grown SrBi ₄ Ti ₄ O ₁₅ Films with Different Orientation. Key Engineering Materials, 0, 368-372, 1811-1813.	0.4	0